

Accepted Manuscript

Title: MoO_x modified ITO/a-Si:H(p) contact for silicon heterojunction solar cell application

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PII: S0025-5408(17)32238-9
DOI: <http://dx.doi.org/10.1016/j.materresbull.2017.09.005>
Reference: MRB 9545

To appear in: *MRB*

Received date: 6-6-2017
Revised date: 1-9-2017
Accepted date: 2-9-2017

Please cite this article as: Jianhua Shi, Leilei Shen, Yongwu Liu, Jian Yu, Jinning Liu, Liping Zhang, Yucheng Liu, Jieyu Bian, Zhengxin Liu, Fanying Meng, MoO_x modified ITO/a-Si:H(p) contact for silicon heterojunction solar cell application, Materials Research Bulletin <http://dx.doi.org/10.1016/j.materresbull.2017.09.005>

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MoO_x modified ITO/a-Si:H(p) contact for silicon heterojunction solar cell application

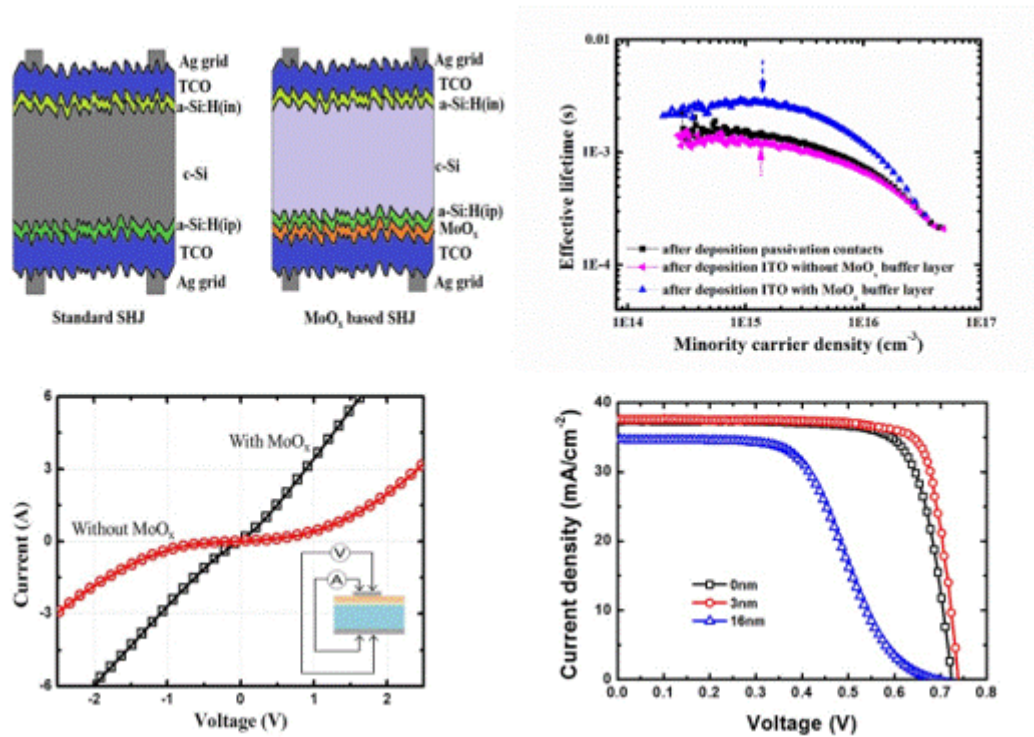
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Graphical abstract:



Highlights:

- Effective carrier lifetime (τ_{eff}) and implied open-circuit voltage (implied V_{oc}) increased abruptly after incorporation MoO_x in SHJ precursor cell.
- Schottky barrier height at interface of ITO/a-Si:H(p) contact decreases after inserting MoO_x buffer layer.
- Absolute V_{oc} gains of 8mV and FF gains of 1.5% are achieved by modifying the ITO/a-Si:H(p) contact

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